

PATENT

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COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231FORM PTO-1449 (Modified)
LIST OF PATENTS AND PUBLICATIONS
FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT
(Use several sheets if necessary)
Sheet 1 of 1In re the application of: Hung Pin Kao, *et al.*

Art Unit: 1746

Serial No. 09/660,992

Examiner: Not Yet Assigned

Filed: August 13, 2000

U.S. PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Patent Number	Date	Name	Class/ Subclass	Filing Date
A1	sl	US4,863,560	9/5/89	Hawkins, W.G.		8/22/88
A2	sl	US5,006,202	4/9/91	Hawkins, W.G., <i>et al.</i>		6/4/90
A3	sl	US5,738,757	4/14/98	Burns, B.E., <i>et al.</i>		11/22/95

FOREIGN PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Filing Date
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OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

Ref. Desig.	Examiner's Initials	
C1		Backlund and Rosengren, "New shapes in (100) Si using KOH and EDP etches," <i>J. Micromach Microeng.</i> 1992, 2:75-79.
C2		Sekimura and Naruse, "Fabrication of 45° optical mirrors on (100) silicon using surfactant-added TMAH solution," <i>International Conference on Solid State Sensors and Actuators</i> , June 7-10, 1999, pp. 550-551, Sedai, Japan.
C3		Strandman, <i>et al.</i> "Fabrication of 45° Mirrors Together With Well-Defined V-Grooves Using Wet Anisotropic Etching of Silicon," <i>J. of Microelectromechanical Systems (MEMS)</i> .
C4		Chang and Hicks, "Mesa structure formation using potassium hydroxide and ethylene diamine based etchants," <i>IEEE Workshop on solid State Sensors and Actuators</i> , pp. 102-103, Hilton Head, SC, June 1988.

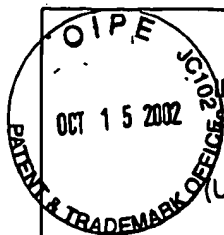
Examiner: Layla SeruDate Considered: 8/6/2004

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.

Cited in
IDS filed
10/15/2002

no date

Cited in
IDS as of 10/15/2002RECEIVED
JAN 23 2001
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
Form PTO-1449 (Modified)
(Use several sheets if necessary)

COMPLETE IF KNOWN

Application Number	09 00,992
Confirmation Number	none
Filing Date	September 13, 2000
First Named Inventor	Kao <i>et al.</i>
Group Art Unit	1746
Examiner Name	unknown
Attorney Docket No.	50225-8048.US00

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Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear
		NUMBER	Kind Code (if known)			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Cite No.	Foreign Patent or Application			Name of Patentee or Applicant of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear	T
		Office	NUMBER	Kind Code (if known)				

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume issue number(s), publisher, city and/or country where published.	T
<i>gl</i>		Backlund <i>et al.</i> , "New shapes in (100) Si using KOH and EDP etches", <i>J. Micromech. Microeng.</i> 2:75-79, 1992.	
<i>gl</i>		Sekimura <i>et al.</i> , "Fabrication of 45° Optical Mirrors on (100) Silicon Using Surfactant-Added TMAH Solution", <i>International Conference on Solid State Sensors and Actuators</i> , pp. 550-551, June 7-10, 1999.	
<i>gl</i>		Chang <i>et al.</i> , "Mesa Structure Formation Using Potassium Hydroxide and Ethylene Diamine Based Etchants", <i>IEEE Workshop on Solid State Sensors and Actuators</i> , pp. 102-103, Hilton Head, SC, June 1988.	
<i>gl</i>		Strandman <i>et al.</i> , "Fabrication of 45° optical mirrors on (100) Si using wet anisotropic etching", <i>Proceedings of the Workshop on Micro Electrical Mechanical Systems (MEMS)</i> , Vol. Workshop 8, pp. 244-249, January 29, 1995.	

EXAMINER <i>Seymour Samuel</i>	DATE CONSIDERED <i>8/6/2004</i>
*EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application(s).	